Abstracts

Highly Reliable InAlAs/InGaAs Heterojunction FETs Fabricated Using Completely Molybdenum-Based Electrode Technology (COMET)

K. Onda, A. Fujihara, E. Mizuki, Y. Hori, H. Miyamoto, N. Samoto and M. Kuzuhara. "Highly Reliable InAlAs/InGaAs Heterojunction FETs Fabricated Using Completely Molybdenum-Based Electrode Technology (COMET)." 1994 MTT-S International Microwave Symposium Digest 94.1 (1994 Vol. I [MWSYM]): 261-264.

This paper describes high performance and high reliability InAlAs/InGaAs Heterojunction FETs fabricated using completely Molybdenum-based electrode technology "COMET", in which a Mo/Ti/Pt/Au Schottky gate and Mo/Ti/Pt/Au non-alloyed ohmic electrodes are successfully employed. The superior reliability of the COMET-FETs is attributed to the reduction of the interdiffusion between metals (gate or ohmic) and semiconductors (InAlAs or InGaAs) by Mo insertion.

❑ Return to main document.